

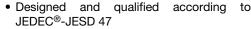
Vishay Semiconductors

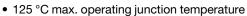
High Voltage Phase Control Thyristor, 12 A



PRIMARY CHARACTERISTICS							
I _{T(AV)} 8 A							
V _{DRM} /V _{RRM}	800 V						
V_{TM}	1.2 V						
I _{GT}	15 mA						
T_J	-40 °C to 125 °C						
Package	TO-220AB 3L						
Circuit configuration	Single SCR						

FEATURES





 Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



APPLICATIONS

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge.

DESCRIPTION

The VS-12TTS08... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS									
Capacitive input filter T _A = 55 °C, T _J = 125 °C, common heatsink of 1 °C/W	13.5	17	А						

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I _{T(AV)}	Sinusoidal waveform	8	^						
I _{T(RMS)}		12.5	Α						
V _{DRM} /V _{RRM}		800	V						
I _{TSM}		110	Α						
V _T	8 A, T _J = 25 °C	1.2	V						
dV/dt		150	V/μs						
dl/dt		100	A/μs						
TJ	Range	-40 to +125	°C						

VOLTAGE RATINGS									
PART NUMBER	V _{RRM} , MAXIMUM PEAK VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA						
VS-12TTS08-M3	800	800	1.0						



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ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Maximum average on-state current	I _{T(AV)}	T 100 °C 100° conduction helf sine ways	8						
Maximum RMS on-state current	I _{T(RMS)}	T _C = 108 °C, 180° conduction, half sine wave	12.5	•					
Maximum peak, one-cycle,		10 ms sine pulse, rated V _{RRM} applied, T _J = 125 °C	95	Α					
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied, T _J = 125 °C	110						
Maximum 12t for fusing	l ² t	10 ms sine pulse, rated V _{RRM} applied, T _J = 125 °C	45	A ² s					
Maximum I ² t for fusing	1-1	10 ms sine pulse, no voltage reapplied, T _J = 125 °C	64						
Maximum I ² √t for fusing	I²√t	$t=0.1$ ms to 10 ms, no voltage reapplied, $T_J=125^{\circ}\text{C}$	640	A²√s					
Maximum on-state voltage drop	V _{TM}	8 A, T _J = 25 °C	1.2	V					
On-state slope resistance	r _t	T _{.I} = 125 °C	16.2	mΩ					
Threshold voltage	V _{T(TO)}		0.87	V					
Maximum reverse and direct leakage	1 /1	$T_J = 25 ^{\circ}\text{C}$	0.05						
current	I _{RM} /I _{DM}	$V_R = Rated V_{RRM}/V_{DRM}$	1.0						
Typical holding current	I _H	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C	30	mA					
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C	50						
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 ^{\circ}\text{C}, V_{DRM} = R_g - k = Open$	150	V/µs					
Maximum rate of rise of turned-on current	dl/dt		100	A/μs					

TRIGGERING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak gate power	P _{GM}		8.0	W				
Maximum average gate power	P _{G(AV)}		2.0	VV				
Maximum peak positive gate current	+ I _{GM}		1.5	Α				
Maximum peak negative gate voltage	- V _{GM}		10	V				
		Anode supply = 6 V, resistive load, T _J = - 65 °C	20	mA				
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	15					
		Anode supply = 6 V, resistive load, T _J = 125 °C	10					
		Anode supply = 6 V, resistive load, T _J = - 65 °C	1.2					
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	1	V				
voltage to trigger		Anode supply = 6 V, resistive load, T _J = 125 °C	0.7	V				
Maximum DC gate voltage not to trigger	V_{GD}	T = 105 °C V = Peted value	0.2					
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value	0.1	mA				

SWITCHING									
PARAMETER SYMBOL TEST CONDITIONS VALUES UN									
Typical turn-on time	t _{gt}	T _J = 25 °C	0.8						
Typical reverse recovery time	t _{rr}	T _{.1} = 125 °C	3	μs					
Typical turn-off time	t _q	1j = 125 C	100						



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THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and storage temperature range		T _J , T _{Stg}		-40 to 125	°C			
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	1.5				
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W			
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5				
Annewiganto weight				2	g			
Approximate weight				0.07	OZ.			
Marinting toward	minimum			6 (5)	kgf · cm			
Mounting torque	maximum			12 (10)	(lbf · in)			
Marking device			Case style TO-220AB 3L	12TTS08				

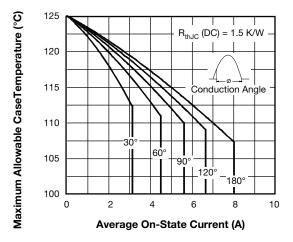


Fig. 1 - Current Ratings Characteristics

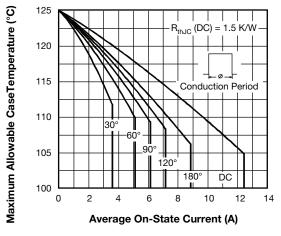


Fig. 2 - Current Ratings Characteristics

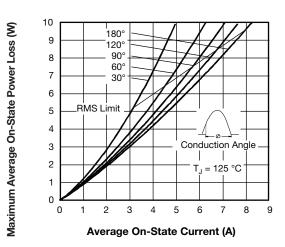


Fig. 3 - On-State Power Loss Characteristics

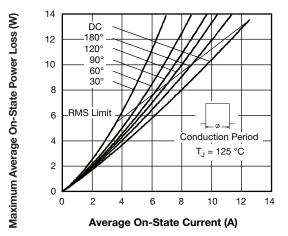


Fig. 4 - On-State Power Loss Characteristics

Peak Half Sine Wave Forward Current (A)

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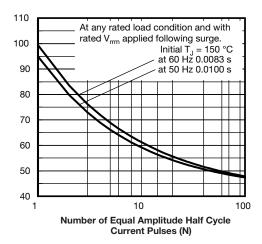


Fig. 5 - Maximum Non-Repetitive Surge Current

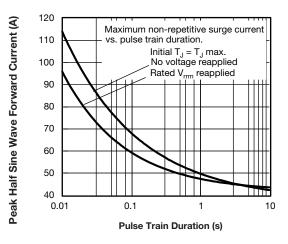


Fig. 6 - Maximum Non-Repetitive Surge Current

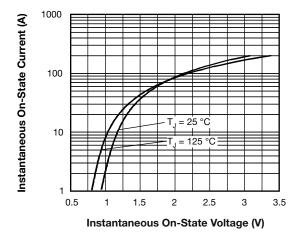


Fig. 7 - On-State Voltage Drop Characteristics

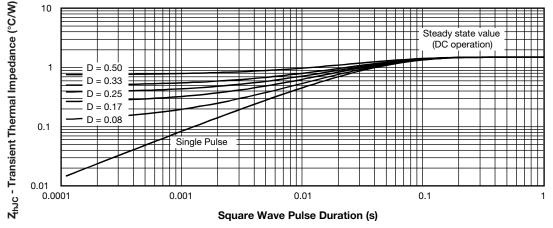


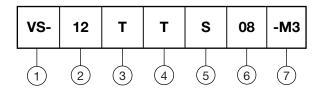
Fig. 8 - Thermal Impedance Z_{thJC} Characteristics



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ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

2 - Current ratings (12 = 12.5 A)

Circuit configuration:

T = single thyristor

4 - Package:

T = TO-220

5 - Type of silicon

S = standard recovery rectifier

6 - Voltage rating (08 = 800 V)

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N BASE QUANTITY PACKAGING DESCRIPTION									
VS-12TTS08-M3	TTS08-M3 50 Antistatic plastic tubes								

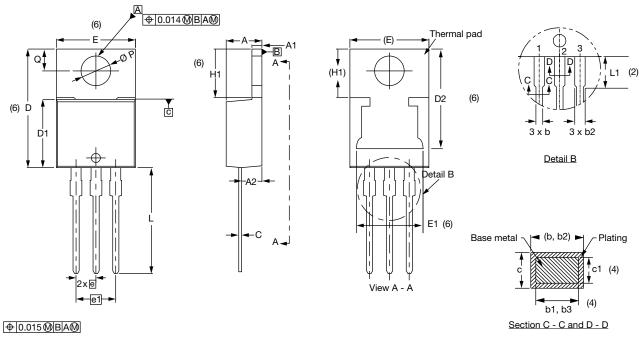
LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?96154						
Part marking information	www.vishay.com/doc?95028						



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TO-220AB 3L

DIMENSIONS in millimeters and inches



Lead tip \	
	1

Conforms to JEDEC® outline TO-220AB

SYMBOL	MILLIN	IETERS	INCHES		NOTES	NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
STWIBUL	MIN.	MAX.	MIN.	MAX.	NOTES		STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183			D2	11.68	13.30	0.460	0.524	6, 7
A1	1.14	1.40	0.045	0.055			E	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			е	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4		e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068			H1	6.09	6.48	0.240	0.255	6
b3	1.14	1.73	0.045	0.068	4		L	13.52	14.02	0.532	0.552	
С	0.36	0.61	0.014	0.024			L1	3.32	3.82	0.131	0.150	2
с1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3		Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355								

Notes

- $^{(1)}$ Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



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